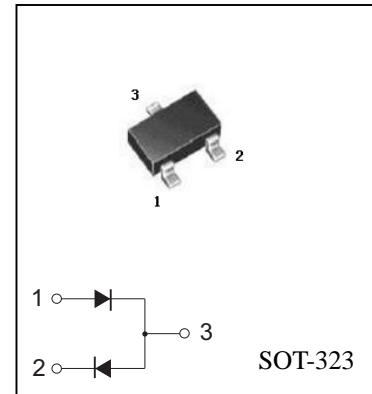


SWITCHING DIODE
BAV99W

FEATURES

- For high-speed switching applications
- Connected in series

Maximum Ratings @Ta=25°C

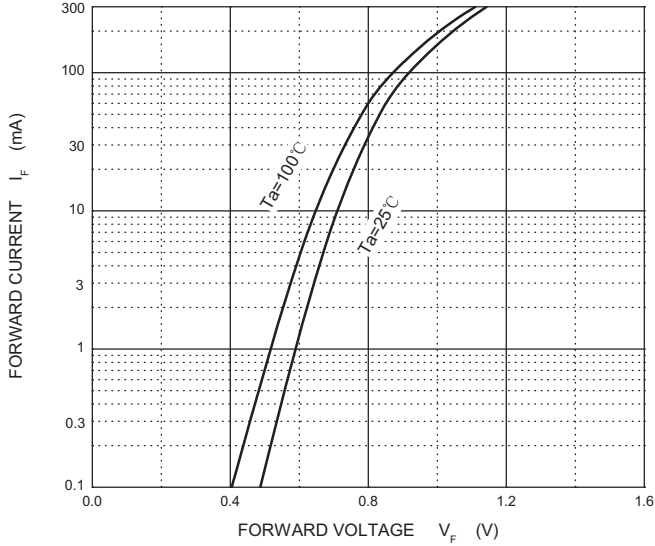
Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	75	V
Forward Current	I_F	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

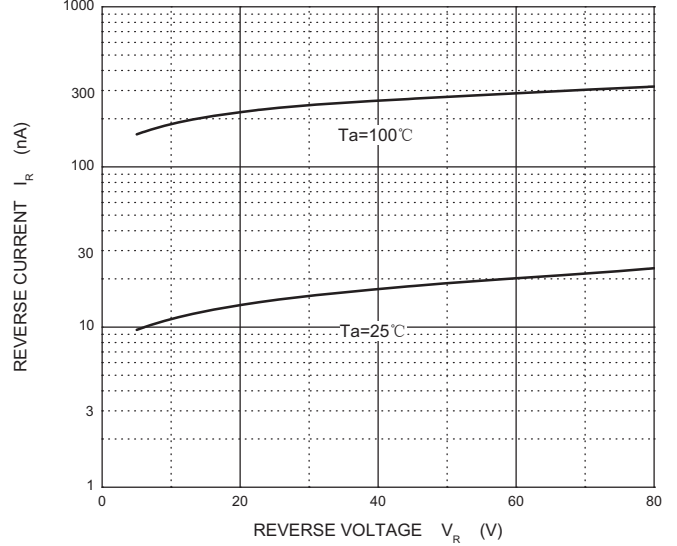
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_{R1}	$V_R=75V$		2.5	μA
	I_{R2}	$V_R=25V$		25	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0$ $f=1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	ns

BAV99W

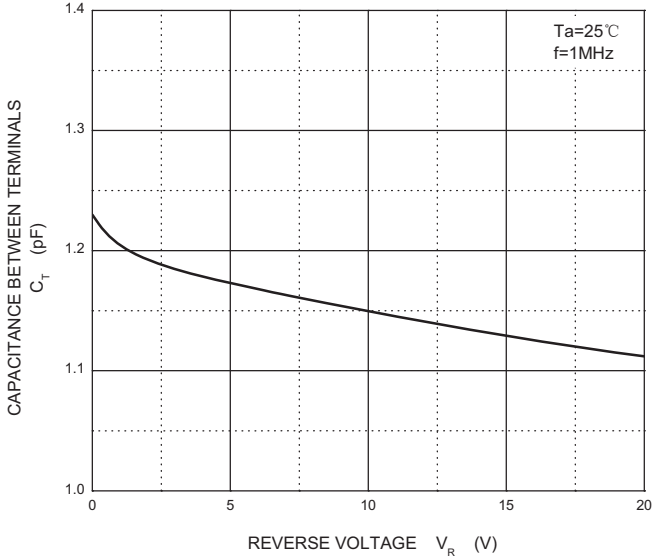
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

